

#### **40V DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub> max (A) T <sub>A</sub> = +25°C
40\/	$25m\Omega$ @ $V_{GS} = -10V$	-7.6
-40V	45mΩ @ V <sub>GS</sub> = -4.5V	-6.0

### **Description**

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Motor Control
- Backlighting
- DC-DC Converters
- Printer Equipment

### **Features and Benefits**

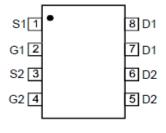
- Low R<sub>DS(on)</sub> Minimizes conduction losses
- Fast switching speed Minimizes switching losses
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

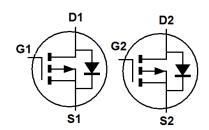
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper lead frame.
   Solderable per MIL-STD-202, Method 208<sup>(3)</sup>
- Weight: 0.074 grams (approximate)







Top View Pin-Out



Device symbol

#### Ordering Information (Notes 4 & 5)

Part Number	Compliance	Case	Packaging
DMP4025LSD-13	Standard	SO-8	2500 / Tape & Reel
DMP4025LSDQ-13	Automotive	SO-8	2500 / Tape & Reel

Notes:

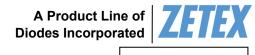
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.
- 5. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.

#### **Marking Information**



DII = Manufacturer's Marking
P4025LD = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 10 = 2010)
WW = Week (01 - 53)





## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-40	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	v	
Continuous Drain Current	V <sub>GS</sub> = -10V	(Notes 7 & 9)	lD	-7.6	
		T <sub>A</sub> = +70°C (Notes 7 & 9)		-6.1	
		(Notes 6 & 9)		-5.8	
		(Notes 6 & 10)		-6.9	Α
Pulsed Drain Current	V <sub>GS</sub> = -10V	(Notes 8 & 9)	I <sub>DM</sub>	-28.0	
Continuous Source Current (Body diode)		(Notes 7 & 9)	I <sub>S</sub>	-3.0	ı
Pulsed Source Current (Body diode)		(Notes 8 & 9)	I <sub>SM</sub>	-28.0	

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

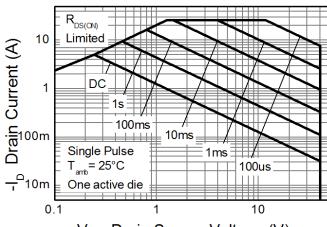
Characteristic		Symbol	Value	Unit	
S	(Notes 6 & 9)		1.25 10	W mW/°C	
Power Dissipation Linear Derating Factor	(Notes 6 & 10)	P <sub>D</sub>	1.8 14.3		
	(Notes 7 & 9)		2.14 17.2		
Thermal Resistance, Junction to Ambient	(Notes 6 & 9)		100		
	(Notes 6 & 10)	R <sub>0JA</sub>	70	°C/W	
	(Notes 7 & 9)		58		
Thermal Resistance, Junction to Lead	(Notes 9 & 11)	R <sub>0JL</sub>	51		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

Notes:

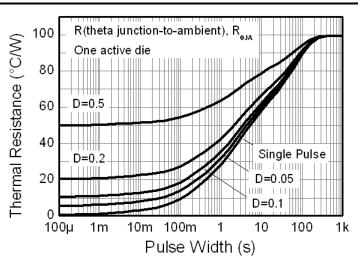
- 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as note (2), except the device is measured at  $t \le 10$  sec. 8. Same as note (2), except the device is pulsed with D = 0.02 and pulse width 300 $\mu$ s.
- 9. For a dual device with one active die.
- 10. For a device with two active die running at equal power.
   11. Thermal resistance from junction to solder-point (at the end of the drain lead).



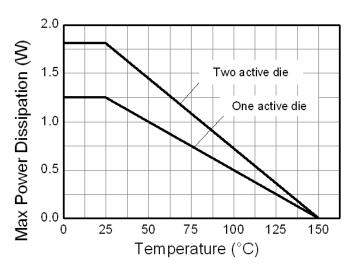
### **Thermal Characteristics**



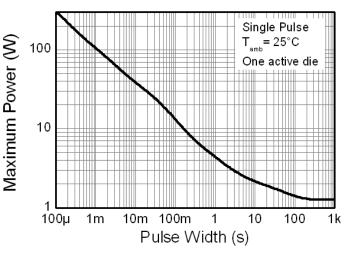
-V<sub>DS</sub> Drain-Source Voltage (V) **P-channel Safe Operating Area** 



# **Transient Thermal Impedance**



**Derating Curve** 



**Pulse Power Dissipation** 



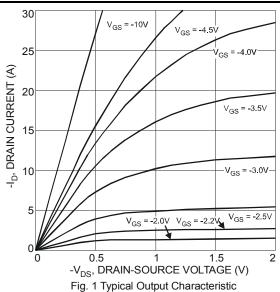
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

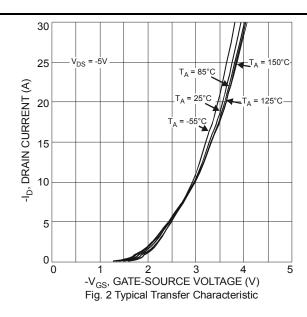
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	_	_	V	I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	-1.0	μΑ	V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	-0.8	-1.3	-1.8	V	I <sub>D</sub> = -250 μA, V <sub>DS</sub> = V <sub>GS</sub>	
Static Drain-Source On-Resistance (Note 12)	Б		18	25	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -3A	
Static Dialii-Source Off-Resistance (Note 12)	R <sub>DS (ON)</sub>	_	30	45	11122	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3A	
Forward Transconductance (Notes 12 & 13)	g <sub>fs</sub>	_	16.6	_	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -3A	
Diode Forward Voltage (Note 12)	$V_{SD}$	_	-0.7	-1.0	V	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V	
DYNAMIC CHARACTERISTICS (Note 13)	DYNAMIC CHARACTERISTICS (Note 13)						
Input Capacitance	C <sub>iss</sub>		1640	_		V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss		179	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>		128	_			
Gate Resistance	$R_g$		6.43	_	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz	
Total Gate Charge (Note 14)	Qg		14.0	_		$V_{GS} = -4.5V$ $V_{DS} = -20V$ $V_{DS} = -3A$	
Total Gate Charge (Note 14)	Qg	_	33.7	_	nC		V <sub>DS</sub> = -20V
Gate-Source Charge (Note 14)	Q <sub>gs</sub>	_	5.5	_	IIC		I <sub>D</sub> = -3A
Gate-Drain Charge (Note 14)	$Q_{gd}$	_	7.3	_			
Turn-On Delay Time (Note 14)	t <sub>D(on)</sub>	_	6.9	_		$V_{DD} = -20V, V_{GS} = -10V$ $I_{D} = -3A$	
Turn-On Rise Time (Note 14)	t <sub>r</sub>	_	14.7	_			
Turn-Off Delay Time (Note 14)	t <sub>D(off)</sub>	_	53.7	_	ns		
Turn-Off Fall Time (Note 14)	t <sub>f</sub>	_	30.9	_			

Notes:

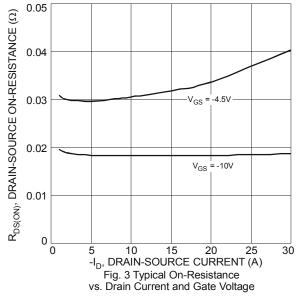
- 12. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
  13. For design aid only, not subject to production testing.
  14. Switching characteristics are independent of operating junction temperatures.

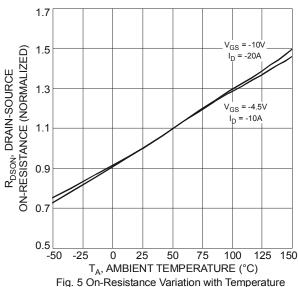
# **Typical Characteristics**











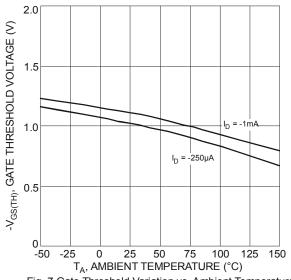
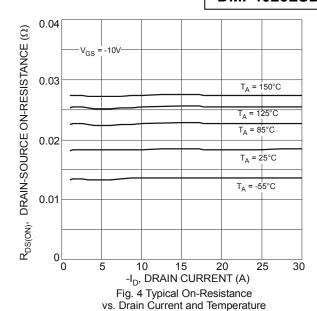


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



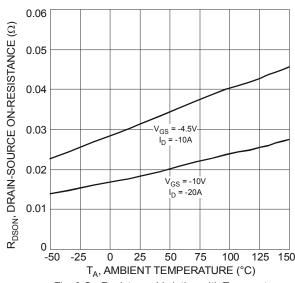


Fig. 6 On-Resistance Variation with Temperature

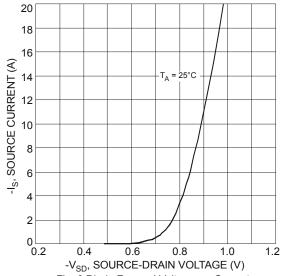
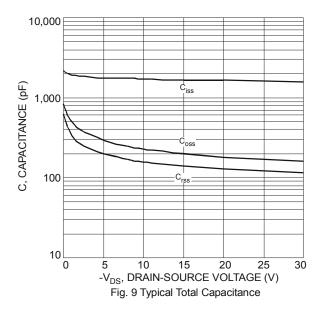
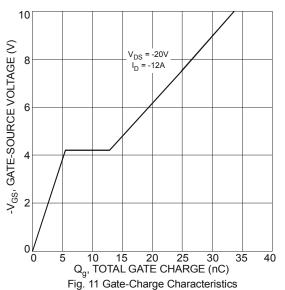
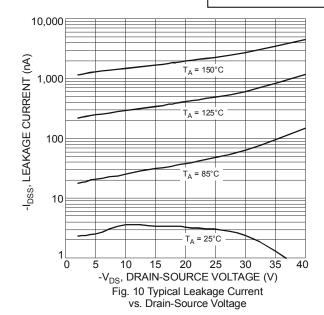


Fig. 8 Diode Forward Voltage vs. Current





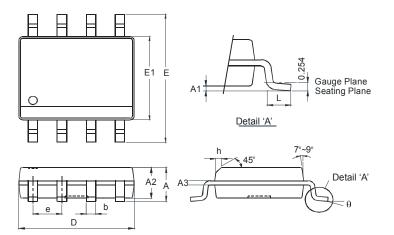






## **Package Outline Dimensions**

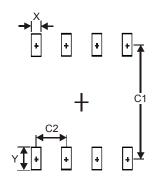
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8				
Dim	Min	Max		
Α	1	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	1	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1 27





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